

## High-Efficiency Blue Organic Light-Emitting Diode Using a 3,5-di(9H-carbazol-9-yl)tetraphenylsilane Host via Solution-Process

### Supporting Information

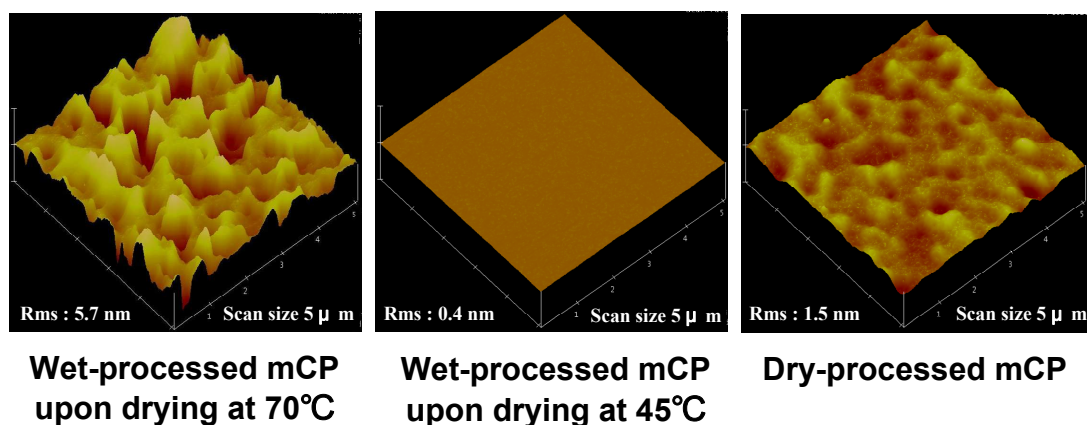
**Device lifetime:** To investigate the lifetime performance of the three studied materials, simple encapsulation has been done on the corresponding blue devices. The lifetime is  $26 \pm 2$  hrs for the SimCP2 containing device, while  $22 \pm 1$  and  $17 \pm 1$  hrs for the SimCP and mCP-containing counterparts. The reasons why the SimCP2 containing device has exhibited a longer lifetime may be attributed to its better robustness due to its higher glass transition temperature and its higher current efficiency.<sup>1</sup>

#### **Effect of fabrication process on the roughness of the mCP-composing film:**

**Fig. S1** shows the atomic-force microscopic (AFM) images of the surface topology of the mCP-composing film via solution-process upon drying at  $70\text{ }^\circ\text{C}$  ( $>T_g$ ,  $55\text{ }^\circ\text{C}$ ), comparing with the one at  $45\text{ }^\circ\text{C}$  ( $<T_g$ ). As seen, the resultant surface upon drying at  $70\text{ }^\circ\text{C}$  is rough, with surface roughness of  $5.7\text{ nm}$ , while the counterpart upon drying at  $45\text{ }^\circ\text{C}$  is relatively smooth, with surface roughness of  $0.6\text{ nm}$ . This indicates that the resultant film is easy to deform, causing spikes on its surface, as the applied drying-temperature ( $70\text{ }^\circ\text{C}$ ) is higher than the  $T_g$  of mCP ( $55\text{ }^\circ\text{C}$ ).<sup>2</sup> Therefore, the rough morphology of the emissive layer would cause serious leakage current, and in

turn damage the device efficiency. However, using a relatively low temperature, for example, 45 °C, in the drying process is not suitable for the device fabrication, since the applied temperature is much lower than the boiling point of solvent (110 °C), which will in turn make the residual solvent difficult to evaporate. Hence, no efficiency result of the mCP-composing device via solution-process upon drying at 45 °C is shown in this report.

**Fig. S1** also shows the AFM image of the surface topology of the mCP-composing film via dry-process. As seen, the resultant surface via solution-process upon drying at 70 °C is rougher than that via dry-process. The rough morphology of the solution-processed mCP film may explain why its resulting device exhibited a comparatively low efficiency if fabricated via wet-process.



**Fig. S1** Atomic-force microscopic (AFM) images of the surface topology of the mCP-composing films upon drying at 70 °C after the solution-process, comparing with that upon drying at 45 °C. Also shown is the dry-processed counterpart. All the films are prepared on the PEDOT: PSS-coated ITO-substrate.

## Reference

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- (2) M. C. Sun, J. H. Jou, W. K. Weng and Y. S. Huang, *Thin Solid Films*, 2005, **491**, 260.